PROCESS CP108

Schottky Rectifier

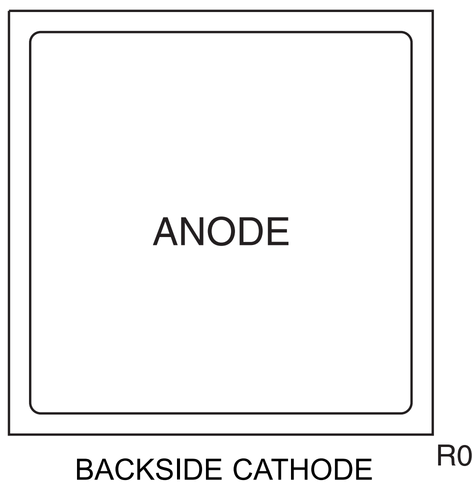
Schottky Barrier Rectifier Chip - 2.0 Amp

Central™
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	52 X 52 MILS
Die Thickness	9 MILS
Anode Bonding Pad Area	47 X 47 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 10,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER
5,110

PRINCIPAL DEVICE TYPES
1N5817
1N5818
1N5819
CXSH-4
CZSH-4

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
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www.centralsemi.com

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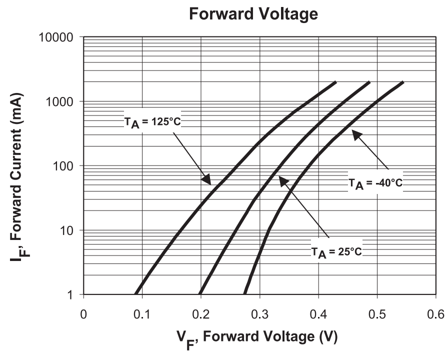
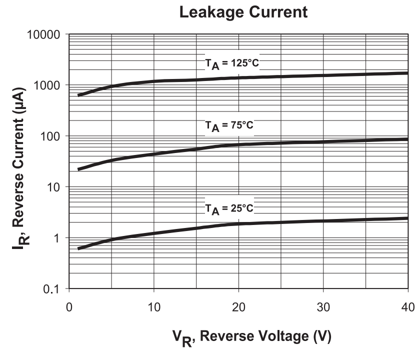
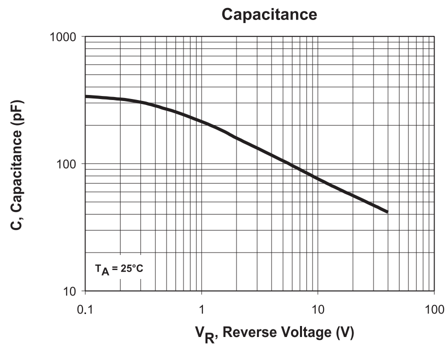
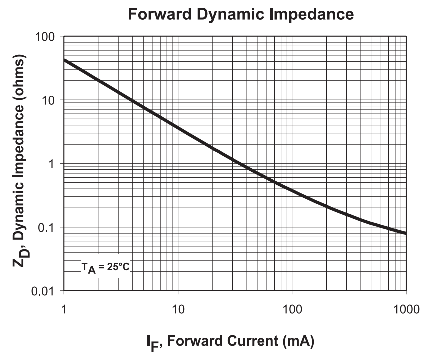
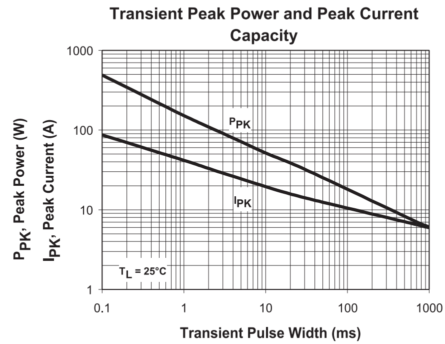
Typical Electrical Characteristics

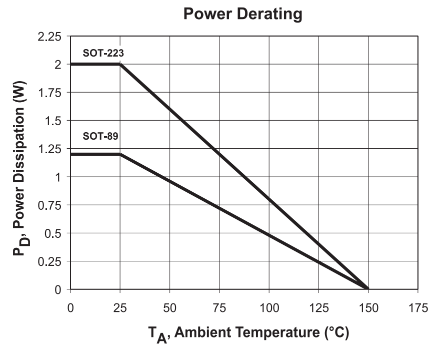












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